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RDS / RBDS Single-chip Signal Processor



Overview

The LC72722PM is a single-chip system IC that implement the signal processing required by the European Broadcasting Union RDS (Radio Data System) standard and by the US NRSC (National Radio System Committee) RBDS (Radio Broadcast Data System) standard. This IC include band-pass filter, demodulator, synchronization, and error correction circuits as well as data buffer RAM on chip and perform effective error correction using a soft-decision error correction technique.

Functions

- Band-pass filter : switched capacitor filter (SCF)
- Demodulator : RDS data clock regeneration and demodulated data reliability information
- Synchronization : Block synchronization detection (with variable backward and forward protection conditions)
- Error correction : Soft-decision/hard-decision error correction
- Buffer RAM : Adequate for 24 blocks of data (about 500 ms) and flag memory
- Data I/O : CCB* interface (power on reset)

Features

- Error correction capability improved by soft-decision error correction
- The load on the control microprocessor can be reduced by storing decoded data in the on-chip data buffer RAM.
- Two synchronization detection circuits provide continuous and stable detection of the synchronization.
- Data can be read out starting with the backward-protection block data after a synchronization reset.
- Fully adjustment free

Specifications

- Operating power-supply voltage : 4.5 to 5.5 V
- Operating temperature : -40 to +85°C
- Package : MFP24 (375 mil)

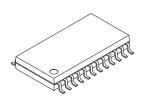
* Computer Control Bus (CCB) is an ON Semiconductor's original bus format and the bus addresses are controlled by ON Semiconductor.

ORDERING INFORMATION

See detailed ordering and shipping information on page 18 of this data sheet.



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SOIC24 W / MFP24 (375 mil)

Specifications Absolute Maximum Ratings at Ta = 25°C, Vssd = Vssa = 0 V

Parameter	Symbol	Pin Name	Ratings	Unit
Maximum supply voltage	Vddmax	Vddd, Vdda	-0.3 to +7.0	V
	Vin1max	CL, DI, CE, SYR, T1, T2, T3, T4, T5, T6, T7, SYNC	-0.3 to +7.0	V
Maximum input voltage	Vin2max	XIN	-0.3 to Vddd+0.3	V
	Vin3max	MPXIN, CIN	-0.3 to Vdda+0.3	V
	Vo1max	DO, SYNC, RDS-ID, T3, T4, T5, T6, T7	-0.3 to +7.0	V
Maximum output voltage	Vo2max	XOUT	-0.3 to Vddd+0.3	V
	Vo3max	FLOUT	-0.3 to Vdda+0.3	V
	lo1max	DO, T3, T4, T5, T6, T7	+6.0	mA
Maximum output current	lo2max	XOUT, FLOUT	+3.0	mA
	lo3max	SYNC, RDS-ID	+20.0	mA
Allowable power dissipation	Pdmax	(Ta ≤ 85°C)	175	mW
Operating temperature	Topr		-40 to +85	°C
Storage temperature	Tstg		–55 to +125	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Allowable Operating Ranges at Ta = -40 to 85°C, Vssd = Vssa = 0 V

Parameter	Symbol	Pin Name	Conditions		Ratings		Unit
i arameter	Symbol	FIII Naille	Contaitionic	min	typ	max	Onit
Supply voltage	Vdd1	Vddd, Vdda		4.5	5.0	5.5	V
Supply voltage	Vdd2	Vddd	Serial data hold voltage	2.0			V
Input high-level voltage	VIH	CL, DI, CE, SYR, T1, T2		0.7Vddd		6.5	V
Input low-level voltage	VIL	CL, DI, CE, SYR, T1, T2		0		0.3Vddd	V
Output voltage	VO	DO, SYNC, RDS-ID, T3, T4, T5, T6, T7				6.5	V
	VIN1		f = 57 ±2 kHz			50	mVrms
Input amplitude	V _{IN2}	MPXIN	100% modulation composite	100			mVrms
	VXIN	XIN		400		1500	mVrms
Guaranteed crystal	XTAL		$CI \le 120 \ \Omega \ (XS = 0)$		4.332		MHz
Oscillator frequencies	XIVE	XIN, XOUT	$CI \le 70 \ \Omega \ (XS = 1)$		8.664		MHz
Crystal oscillator frequency deviation	TXtal	XIN, XOUT	fo = 4.332 MHz, 8.664 MHz			±100	ppm
Data setup time	tSU	DI, CL		0.75			μS
Data hold time	tHD	DI, CL		0.75			μS
Clock low level time	tCL	CL		0.75			μS
Clock high level time	tCH	CL		0.75			μs
CE wait time	tEL	CE, CL		0.75			μS
CE setup time	tES	CE, CL		0.75			μS
CE hold time	tEH	CE, CL		0.75			μS
CE high-level time	tCE	CE				20	ms
Data latch change time	tLC					1.15	μS
Data output time	tDC	DO,CL	Differs depending on the value of the pull-up			0.46	μS
	tDH	DO,CE	resistor used.			0.46	μS

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

Electrical Characteristics at Ta = -40	to 85°C, Vssd = Vssa = 0 V
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Demonster	O makes	Pin Name				1.1	
Parameter	Symbol		Conditions	min	typ	max	Unit
Input resistance	R _{MPXIN}	MPXIN-Vssa	f = 57 kHz		43.0		kΩ
	Rcin	C _{IN} -Vssa	f = 57 kHz		100.0		kΩ
Internal feedback resistance	Rf	XIN			1.0		MΩ
Center frequency	fc	FLOUT		56.5	57.0	57.5	kHz
–3 dB band width	BW-3dB	FLOUT		2.5	3.0	3.5	kHz
Gain	Gain	MPXIN-FLOUT	f = 57 kHz	28	31	34	dB
	Att1	FLOUT	∆f = ±7 kHz	30			dB
Stop band Attenuation	Att2	FLOUT	f < 45 kHz, f > 70 kHz	40			dB
	Att3	FLOUT	f < 20 kHz	50			dB
Reference voltage output	Vref	Vref	Vdda = 5.0 V		2.5		V
Hysteresis	V _{HIS}	CL, DI, CE, SYR, T1, T2			0.1Vddd		V
Output low-level	V _{OL1}	DO, T3, T4, T5, T6, T7	I = 2 mA			0.5	V
voltage	V _{OL2}	SYNC, RDS-ID	I = 8 mA			0.5	V
Input high-level	I _{IH1}	CL, DI, CE, SYR, T1, T2	V _I = Vddd			5.0	μA
current	I _{IH2}	XIN	V _I = Vddd	2.0		11.0	μA
Input low-level	I _{IL1}	CL, DI, CE, SYR, T1, T2	V _I = 0 V			5.0	μA
current	I _{IL2}	XIN	V _I = 0 V	2.0		11.0	μA
Output off leakage current	IOFF	DO, SYNC, RDS-ID, T3, T4, T5, T6, T7	V _O = 6.5 V			5.0	μA
Current drain	ldd	Vddd, Vdda			9		mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

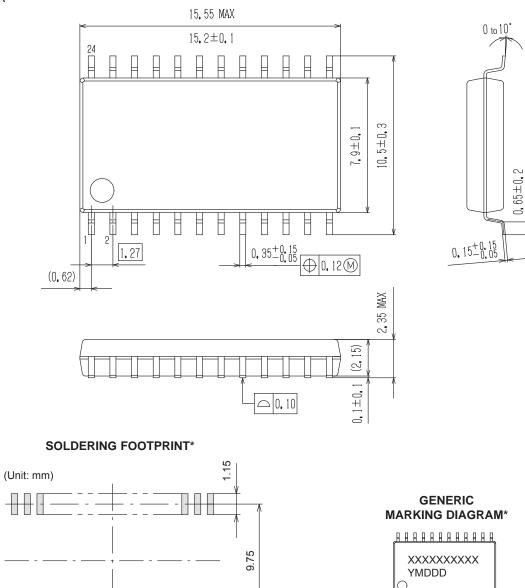
Package Dimensions

unit : mm

SOIC24 W / MFP24 (375 mil)

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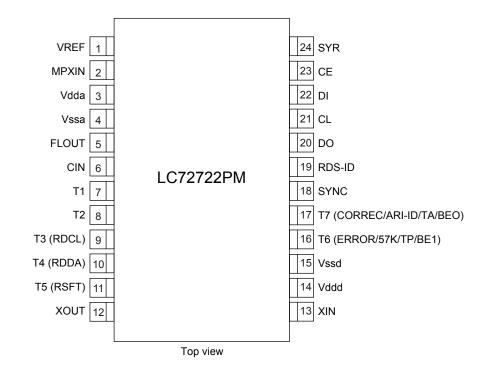


NOTE: The measurements are not to guarantee but for reference only.

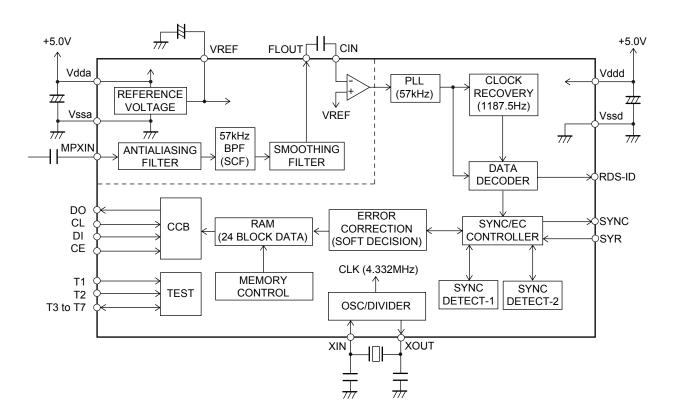
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

XXXXX = Specific Device Code Y = Year M = Month DDD = Additional Traceability Data

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present.



Block Diagram



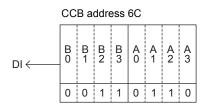
Pin Functions

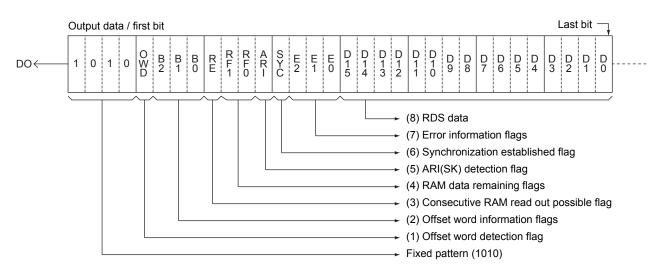
D's No.		F	I/O	
Pin No.	Pin name	Function	10	Pin circuit
1	VREF	Reference voltage output (Vdda/2)	Output	↑Vdda ↓ ↓ ↓ Vssa
2	MPXIN	Baseband (multiplexed) signal input	Input	Vdda
5	FLOUT	Subcarrier output (filter output)	Output	
7	CIN	Subcarrier input (comparator input)	Input	Vdda Vssa WREF
3	Vdda	Analog system power supply (+5V)	-	_
4	Vssa	Analog system ground	_	-
12	XOUT	Crystal oscillator output (4.332/8.664MHz)	Output	^Vddd
13	XIN	Crystal oscillator input (external reference signal input)		XIN XOUT WSsd
7	T1	Test input (This pin must always be connected to ground.)	Input	
8	Т2	Test input (standby control) 0:Normal operation, 1:Standby state (crystal oscillator stopped)		Vssd
9	T3(RDCL)	Test I/O (RDS clock output)		
10	T4(RDDA)	Test I/O (RDS data output)		
11	T5(RSFT)	Test I/O (soft-decision control data output)		
16	T6 (ERROR/57K/BE1)	Test I/O (error status, regenerated carrier, error block count)	I/O*	
17	T7 (CORREC/ARI-ID/BE0)	Test I/O (error correction status, SK detection, error block count)		
18	SYNC	Block synchronization detection output		
19	RDS-ID	RDS detection output	Output	
20	DO	Data output		Vssd
21	CL	Clock input – Serial data interface (CCB)		
22	DI	Data input	Input	
23	CE	Chip enable		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,
24	SYR	Synchronization and RAM address reset (active high)		
14	Vddd	Digital system power supply (+5V)	_	_
15	Vssd	Digital system ground	-	-

Note : * Normally function as an output pin. Used as an I/O pin in test mode, which is not available to user applications.

CCB output data format

- 1. Each block of output data consists of 32 bits (4 bytes), of which 2 bytes are RDS data and 2 bytes are flag data.
- 2. Any number of 32-bits output data blocks can be output consecutively.
- 3. When there is no data that can be read out in the internal memory, the system outputs blocks of all-zero data consecutively.
- 4. If data readout is interrupted, the next read operation starts with the 32-bit data block whose readout was interrupted. However, if only the last bit is remaining to be read, it will not be possible to re-read that whole block.
- 5. The check bits (10 bits) are not output.
- 6. The data valid (OWD) must not be referred to.
- 7. When the first leading bits are not "1010", the read in data is in invalid, and read operation is cancelled.





(1) Offset word detection flag (1bit) : OWD

OWD	Offset word detection
1	Detected
0	Not detected (protection function operating)

(2) Offset word information flag (3bit) : B0 to B2

	В 1		Offset word
0	0	0	А
0	0	1	В
0	1	0	С
0	1	1	C'
1	0	0	D
1	0	1	Е
1	1	0	Unused
1	1	1	Unused

(3) Consecutive RAM read out possible flag (1bit) : RE

RE	RAM data information
1	The next data to be read out is in RAM
0	This data item is the last item in RAM, ant the next data is not present.

(4) RAM data remaining flag (2bits) : RF0,RF1

RF1	RF0	Remaining data in RAM (number of blocks)
0	0	1 to 7
0	1	8 to 15
1	0	16 to 23
1	1	24

Caution : This value is only meaningful when RE is 1. When RE is 0, there is no data in RAM, even if RF is 00. If a synchronization reset was applied using SYR, then the backward protection block data that was written to memory is also counted in this value.

(5) ARI(SK) detection flag (1bit) : ARI

ARI	SK signal
1	Detected
0	Not detected

(6) Synchronization established flag (1bit) : SYC

SYC	Synchronization detection
1	Synchronized
0	Not synchronized

Caution : This flag indicates the synchronization state of the circuit at the point when the data block being output was received. On the other hand, the SYNC pin (pin18) output indicates the current synchronization state of the circuit.

E 2	E 1	Е 0	Number of bits corrected
0	0	0	0 (no errors)
0	0	1	1
0	1	0	2
0	1	1	3
1	0	0	4
1	0	1	5
1	1	0	Correction not possible
1	1	1	Unused

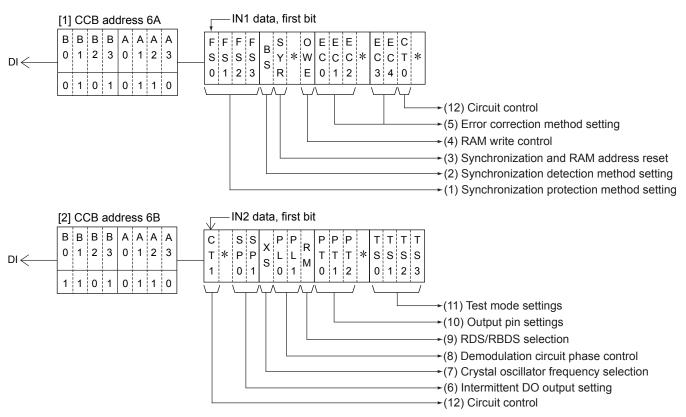
(7) Error information flags (3bits) : E0 to E2

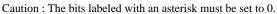
Caution : If the number of errors exceeds the value of the EC0 to EC2 setting (see the section on the CCB input format), the error information flags will be set to the "Correction not possible" value.

(8) RDS data (16bits) : D0 to D15

This data is output with the MSB first ant the LSB last. Caution : When error correction was not possible, the input data is output without change.

CCB Input data format





- (1) Synchronization protection (forward protection) method setting (4bits) : FS0 to FS3
 - FS3 = 0: If offset words in the correct order could not be detected continuously during the number of blocks specified by FS0 to FS2, take that to be a lost synchronization sate.
 - FS3 = 1 : If blocks with uncorrectable errors were received consecutively during the number of blocks specified by FS0 to FS2, take that to be a lost synchronization state.

F S 0	F S 1	F S 2	Condition for detecting lost synchronization
0	0	0	If 3 consecutive blocks matching the FS3 condition are received.
1	0	0	If 4 consecutive blocks matching the FS3 condition are received.
0	1	0	If 5 consecutive blocks matching the FS3 condition are received.
1	1	0	If 6 consecutive blocks matching the FS3 condition are received.
0	0	1	If 8 consecutive blocks matching the FS3 condition are received.
1	0	1	If 10 consecutive blocks matching the FS3 condition are received.
0	1	1	If 12 consecutive blocks matching the FS3 condition are received.
1	1	1	If 16 consecutive blocks matching the FS3 condition are received.

Initial value : FS0 = 0, FS1 = 1, FS2 = 0, FS3 = 0

(2) Synchronization detection method setting (1bit) : BS

BS	Synchronization detection conditions
0	If during 3 blocks, 2 blocks of offset words were detected in the correct order.
1	If the offset words were detected in the correct order in 2 consecutive blocks.

Initial value : BS = 0

(3) Synchronization and RAM address reset (1bit) : SYR

SYR	Synchronization detection circuit	RAM				
0	Normal operation (reset cleared)	Normal write (See the description of the OWE bit)				
1	Forced to the unsynchronized state (synchronization reset)	After the reset is cleared, start writing from the data prior to the establishment of synchronization, i.e. the data in backward protection.				

Initial value : SYR = 0

- <u>The SYR pin (pin24) also provides an identical reset control operation</u>. Applications can use either method. However, <u>the control method that is not used must be set to 0 at all times</u>. Any pulse with a width of over 250 ns will suffice.
- A reset must be applied immediately after the reception channel is changed.
 If a reset is not applied, reception data from the previous channel may remain in on-chip memory.
- 4. Data read out after a synchronization reset is read out starting with the backward protection block data preceding the establishment of synchronization.

(4) RAM write control (1bit) : OWE

OWE	RAM write conditions
0	Only data for which synchronization had been established is written.
1	Data for which synchronization not has been established (unsynchronized data) is also written. (However, this applies when $SYR = 0$.)

Initial value : OWE = 0

(5) Error correction method setting (5bits) : EC0 to EC4

-			1			
E	E	E				
С	С	С	Number of bits corrected			
0	1	2				
0	0	0	0 (error detection only)			
1	0	0	1 or fewer bits			
0	1	0	2 or fewer bits			
1	1	0	3 or fewer bits			
0	0	1	4 or fewer bits			
1	0	1	5 or fewer bits			
0	1	1	Illegal value			
1	1	1	Illegal value			

Е	Е	
С	С	Soft-decision setting
3	4	C
0	0	MODE0 Hard decision
1	0	MODE1 Soft decision A
0	1	MODE2 Soft decision B
1	1	Illegal value

Initial values : EC0 = 0, EC1 = 1, EC2 = 0, EC3 = 0, EC4 = 1

Caution: 1. If soft-decision A or soft-decision B is specified, soft-decision control will be performed even if the number of bits corrected is set to 0 (error detection only). With these settings, data will be output for blocks with no errors.

2. As opposed to soft-decision B, the soft-decision A setting suppresses soft decision error correction.

(6) Intermittent DO output setting

SP0	SP1	DO output state					
0	0	DO goes low when one or more blocks of data are written to memory.					
1	0	DO goes low when 4 or more blocks of data are written to memory.					
0	1	DO goes low when 8 or more blocks of data are written to memory.					
1	1	DO goes low when 12 or more blocks of data are written to memory.					
Initial values : $SPO = 0$, $SP1 = 0$							

Caution: 1. To apply a synchronization reset, set SYR to 1 temporarily using CCB, and then set it back to 0 again using CCB. The circuit will start synchronization capture operation at the point SYR is set to 0.

(7) Crystal oscillator frequency selection (1bit) : XS

XS = 0 : 4.332MHz (Initial value : XS = 0) XS = 1 : 8.664MHz

(8) Demodulation circuit phase control (2bits) : PL0, PL1

PL0	PL1	Demodulation circuit phase control
0	0/1	< Normal operation > when ARI presence or absence is unclear.
	0	If the circuit determines that the ARI signal is absent : 90° phase
1	1	If the circuit determines that the ARI signal is present : 0° phase

Initial values : PL0 = 0, PL1 = 1

- Caution: 1. When PL0 is 0 (normal operation), the IC detects the presence or absence of the ARI signal and reproduces the RDS data by automatically controlling the demodulation phase with respect to the reproduced carrier. However, the initial phase following a synchronization reset is set by PL1.
 - 2. If PL0 is set to 1, the demodulation circuit phase is locked according to the PL1 setting at either 90° (PL1 = 0) or 0° (PL1 = 1), allowing RDS data to be reproduced. When ARI is not present, PL1 should be set to 0, since the RDS data is reproduced by detecting at a phase of 90° with respect to the reproduced carrier. When ARI is present, PL1 should be set to 1, since detection is at 0°. In cases where the ARI presence is known in advance, more stable reproduction can be achieved by fixing the demodulation phase in this manner.

(9) RDS/RBDS(MMBS) selection (1bit) : RM

RM	RBDS	Decoding method
0	None	Only RDS data is decoded correctly (Offset word E is not detected.)
1	Provided	RDS and MMBS data is decoded correctly (Offset word E is also detected.)

Initial value : RM=0

(10) Output pin settings (3bits) : PT0 to PT2 These bits control the T3, T4, T5, T6, T7, SYNC, and RDS-ID pins

	P P P	T3	T4	T5		T6		÷		T7		
MODE	T T T 0 1 2	RDCI	RDDA	RSFT	ERROR	57K	ТР	BE1	CORREC	ARI-ID	TA	BE0
0	0 0 0	-	-	_	-	-		_	_	_	_	-
1	1 0 0	_	_	_	-	_		_	-	_	0	-
2	0 1 0	0	0	0	-	0		_	-	0	_	-
3	1 1 0	0	0	0	0	_		_	0	_	_	-
4	0 0 1	_	_	_	-	_		0	-	_	_	0
5	1 0 1	_	0	0	-	_	•	_	-	_	•	-
6	0 1 1	0	0	0	-	•		_	-	•	_	-
7	1 1 1	0	0	0	•	_		_	•	_	_	-

- : open, \bigcirc , ● : Output enabled (● = reverse polarity)

Initial value : PT0 = 1, PT1 = 1, PT2 = 0 (Mode 3)

Caution: 1. When PT2 is set to 1, the polarity of the T6(ERROR/57K/TP), T7(CORREC/ARI-ID/TA), SYNC, and RDS-ID pins changes to active high.

2. The output pins (T3 to T7, SYNC, and RDS-ID) are all open-drain pins, and require external pull-up resistors to output data.

Mode1 (PT2 = 0)	Pin T6 (TP)			
TP = 0 detected	High (1)			
TP = 1 detected	Low (0)			
TD - Troffic program code				

TP = Traffic program code

Mode1 ($PT2 = 0$)	Pin T7 (TA)
TA = 0 detected	High (1)
TA = 1 detected	Low (0)

TA = Traffic announcement code

Mode2 (PT2 = 0)	Pin T7 (ARI-ID)	
No SK	High (1)	
SK present	Low (0)	

Mode3 (PT2 = 0)	Pin T6 (ERROR)	Pin T7 (CORREC)
Correction not possible	Low (0)	Low (0)
Errors corrected	High (1)	Low (0)
No errors	High (1)	High (1)

Mode = 4 Number of error blocks (B)	Pin T6 (BE1)	Pin T7 (BE0)
B=0	Low (0)	Low (0)
$1 \le B \le 20$	Low (0)	High (1)
$20 < B \le 40$	High (1)	Low (0)
$40 < B \le 48$	High (1)	High (1)

These pins indicate the number of blocks in a set of 48 blocks that had errors before correction. The output polarity of these pins is fixed at the values listed in the table.

Mode (PT2 = 0)	The SYNC pin	
0 to 2	When synchronized : Low (0), When unsynchronized: High (1)	
3	When synchronized : Goes high for a fixed period (421 μ s) at the start of a block and then goes low. When unsynchronized : High (1)	

Caution : The output indicates the synchronization state for the previous block.

When $PT2 = 0$	The RDS-ID pin	
No RDS	High (1)	
RDS present	Low (0)	

(11) Test mode settings (4bits) : TS0 to TS3

Initial values : TSO = 0, TS1 = 0, TS2 = 0, TS3 = 0

(Applications must set these bits to the above values.)

Notes : The T1 and T2 pins (pins 7 and 8) are related to test mode as follows.

Pin T1	Pin T2	IC operation	Notes
0	0	Normal operating mode	These states are user settable
0	1	Standby mode (crystal oscillator stopped)	These states are user settable
1	0/1	IC test mode	Users cannot use this state

The T1 pin must be tied to V_{SS} (0V).

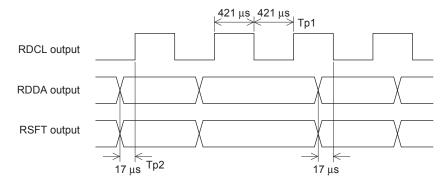
(12) Circuit control (2 bits) : CT0 and CT1

	Item	Control	
CT0	RSFT control	When set to 1, soft-decision control data (RSFT) is easier to generate.	
CT1	RDS-ID detection condition	When set to 1, the RDS-ID detection conditions are made more restrictive.	

Initial value : CT0 = 0, CT1 = 0

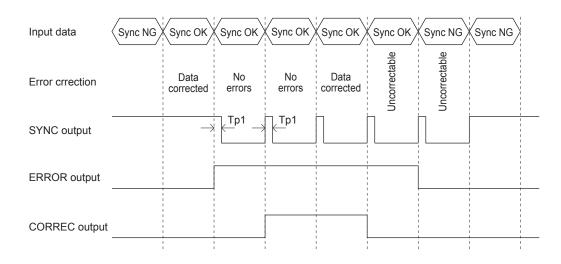
RDCL / RDDA / RSFT and ERROR / CORREC / SYNC output timing

(1) Timing 1



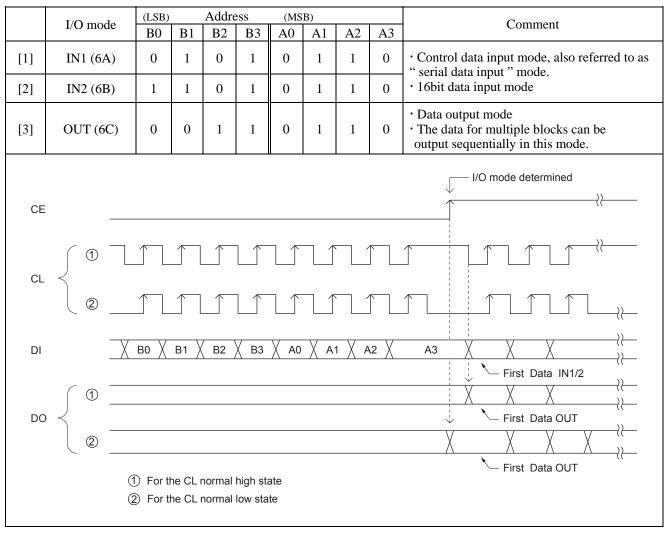
Note : When PT2 = 0, RDDA and RSFT must be acquired on the falling edge of RDCL.

(2) Timing 2 (mode 3, PT2 = 0)



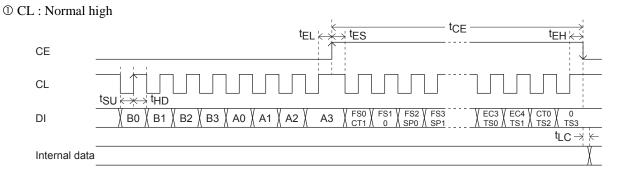
Serial Data Input and Output Methods

Data is input and output using the CCB (Computer Control Bus), which is Our audio IC serial bus format. This IC adopts an 8-bit address CCB format.

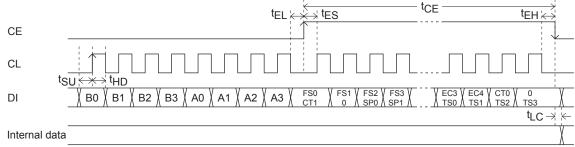


(1) Serial data input (IN1 / IN2)

tSU, tHD, tEL, tES, tEH $\ge 0.75 \mu s$ tLC $< 1.15 \mu s$ tCE < 20 m s



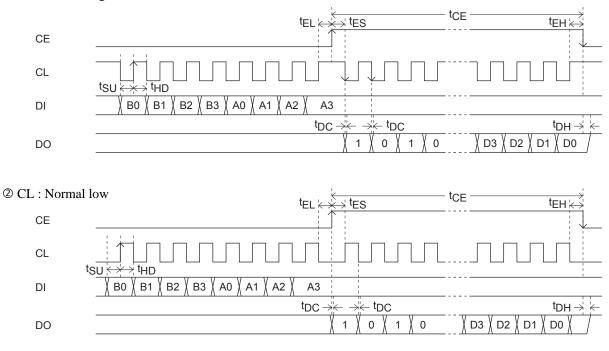
2 CL : Normal low



(2) Serial data output (OUT)

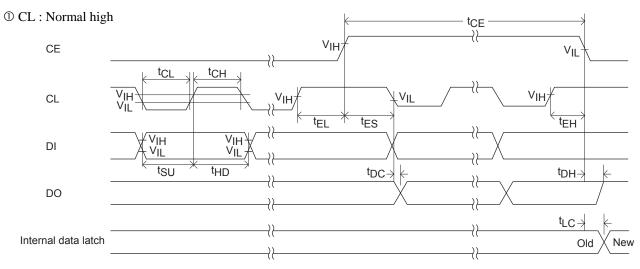
tSU, tHD, tEL, tES, tEH $\ge 0.75 \mu s$ tDC, tDH $< 0.46 \mu s$ tCE < 20 ms

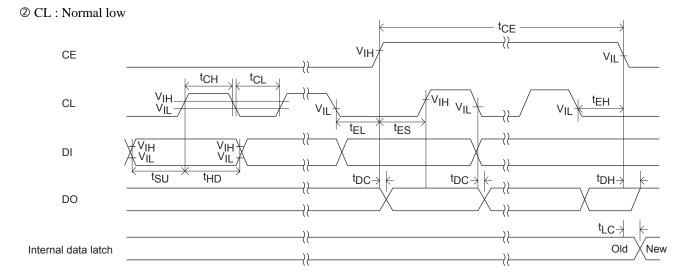
① CL : Normal high



- Cautions : 1. Since the DO pin is an n-channel open-drain output, the transition times (t_{DC}, t_{DH}) will differ with the value of the pull-up resistor used.
 - 2. The CE, CL, DI, and DO pins can be connected to the corresponding pins on other ICs that use the CCB interface. (However, we recommend connecting the DO and CE pins separately if the number of available microcontroller ports allows it.)
 - 3. Serial data I/O becomes possible after the crystal oscillator starts oscillation.

(3) Serial data timing





Parameter	Symbol	Conditions		min	typ	max	Unit
Data setup time	tSU	DI, CL		0.75			μs
Data hold time	tHD	DI, CL		0.75			μs
Clock low level time	tCL	CL		0.75			μs
Clock high level time	tCH	CL	CL				μs
CE wait time	tEL	CE, CL		0.75			μs
CE setup time	tES	CE, CL		0.75			μs
CE hold time	tEH	CE, CL		0.75			μs
CE high level time	tCE	СЕ				20	ms
Data latch transition time	tLC					1.15	μs
Data output time	tDC	DO, CL	Differs with the value of the pull-up			0.46	μs
	^t DH	DO, CE	resistor used.			0.46	μs

DO pin operation

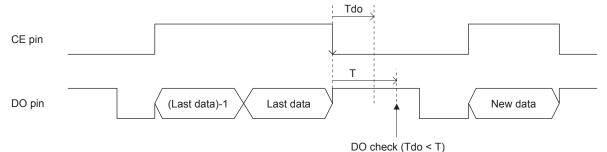
This IC incorporates a RAM data buffer that can hold up to 24 blocks of data. At the point when one block of data is written to this RAM, the IC issues a read request by switching the DO pin from high to low.

The DO pin always goes high for a fixed period (Tdo = $265 \ \mu s$) after a readout and CE goes low. When all the data in the data buffer has been read out, the DO pin is held in the high state until a new block of data has been written to the RAM. If there is data that has not yet been read remaining in the data buffer, the DO pin goes low after the Tdo time has elapsed.

After a synchronization reset, the DO pin is held high until synchronization is established. It goes low at the point the IC synchronizes.

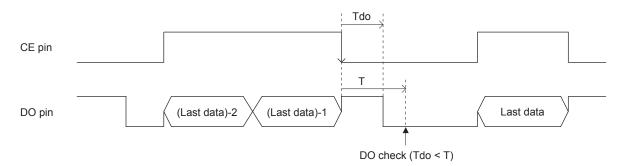
 \textcircled When the DO pin is high following the 265 µs period (Tdo) after data is read out.

Here, the buffer is in the empty state, i.e. the state where new data has not been written. After this, when the DO pin goes low, applications are guaranteed to be able to read out that data without it being overwritten by new data if they start a readout operation within 480 ms of DO going low.



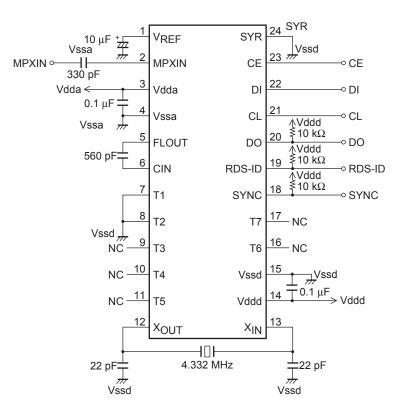
^② When DO goes low 265 µs after data is read out

Here, there is data that has not been read out remaining in the data buffer. In this case, applications are guaranteed to be able to read out that data without it being overwritten by new data if they start a readout operation within 20 ms of DO going low. (Note that this is the worst case condition.)



- Notes: 1. Although an application can determine whether or not there is data remaining in the buffer by checking the DO level with the above timing, checking the RE and RF flags in the serial data is a preferable method.
 - 2. Applications are not limited to reading out one block of data at a time, but rather can read out multiple blocks of data continuously as described above. When using this method, if an application references the RE and RF flags in the data while reading out data, it can determine the amount of data remaining. However, the length of the period for data readout (the period the CE pin remains high) must be kept under 20 ms.
 - 3. If the DO pin is shared with other ICs that use the CCB interface, the application must identify which IC issued the readout request. One method is to read out data from the LC72722PM and either check whether meaningful data has been read (if the LC72722PM is not requesting a read, data consisting of all zeros will be read out) or check whether the DO level goes low within the 256 μs following the completion of the read (if the DO pin goes low, then the request was from another IC).

Sample Application circuit



Caution : 1. Determine the value of the DO pin pull-up resistor based on the required serial data transfer speed. 2. If the SYR pin is unused, it must be connected to ground.

ORDERING INFORMATION

Device	Package	Shipping (Qty / Packing)	
LC72722PM-MPB-E	SOIC24 W / MFP24 (375mil) (Pb-Free)	25 / Fan-Fold	
LC72722PM-TLM-E	SOIC24 W / MFP24 (375mil) (Pb-Free)	1000 / Tape & Reel	

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

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